BL GALAXY ELECTRICAL

ERB12-01---ERB12-10

PLASTIC SILICON RECTIFIERS

VOLTAGE RANGE: 50 --- 1000 V
CURRENT: 1.0 A

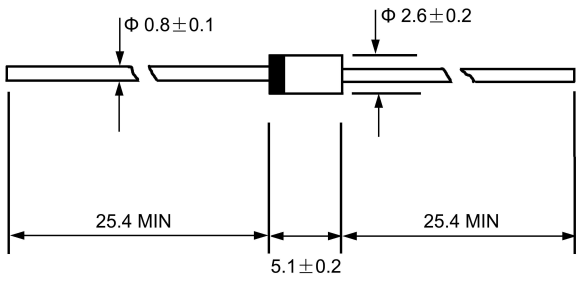
FEATURES

- ◇ Low cost
- ◇ Diffused junction
- ◇ Low leakage
- ◇ Low forward voltage drop
- ◇ High current capability
- ◇ Easily cleaned with Freon,Alcohol,Isopropanol and similar solvents
- ◇ The plastic material carries U/L recognition 94V-0

MECHANICAL DATA

- ◇ Case:JEDEC DO--41,molded plastic
- ◇ Terminals: Axial lead ,solderable per MIL- STD-202,Method 208
- ◇ Polarity: Color band denotes cathode
- ◇ Weight: 0.012ounces,0.34 grams
- ◇ Mounting position: Any

DO - 41



Dimensions in millimeters

MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Ratings at 25℃ ambient temperature unless otherwise specified.

Single phase,half wave,60 Hz,resistive or inductive load. For capacitive load,derate by 20%.

		ERB12 -01	ERB12 -02	ERA12 -04	ERB12 -06	ERB12 -10	UNITS
Maximum recurrent peak reverse voltage	V_{RRM}	100	200	400	600	1000	V
Maximum RMS voltage	V_{RMS}	70	140	280	420	700	V
Maximum DC blocking voltage	V_{DC}	100	200	400	600	1000	V
Maximum average forward rectified current 9.5mm lead length, @T_A=75℃	$I_{F(AV)}$	1.0					A
Peak forward surge current 8.3ms single half-sine-wave superimposed on rated load @T_J=125℃	I_{FSM}	60.0					A
Maximum instantaneous forward voltage @ 1.0 A	V_F	1.1					V
Maximum reverse current @T_A=25℃	I_R	5.0					μA
at rated DC blocking voltage @T_A=100℃		50.0					
Typical junction capacitance (Note1)	C_J	15					pF
Typical thermal resistance (Note2)	$R_{\theta JA}$	50					℃/W
Operating junction temperature range	T_J	- 55---- + 150					℃
Storage temperature range	T_{STG}	- 55 ---- +150					℃

NOTE: 1. Measured at 1.0MHz and applied reverse voltage of 4.0V DC.

2. Thermal resistance from junction to ambient.

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FIG.1 -- TYPICAL FORWARD CHARACTERISTIC

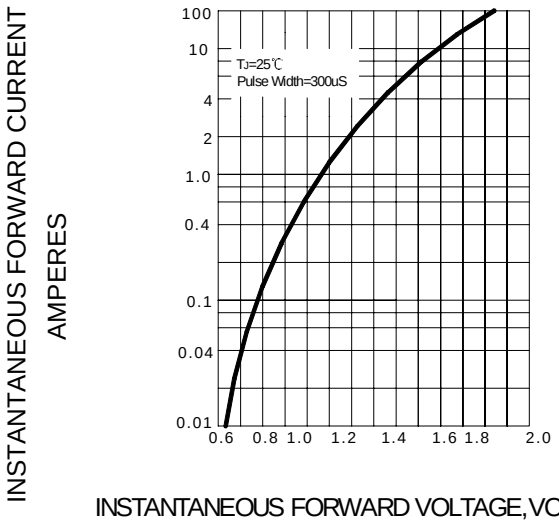

FIG.2 -- TYPICAL JUNCTION CAPACITANCE

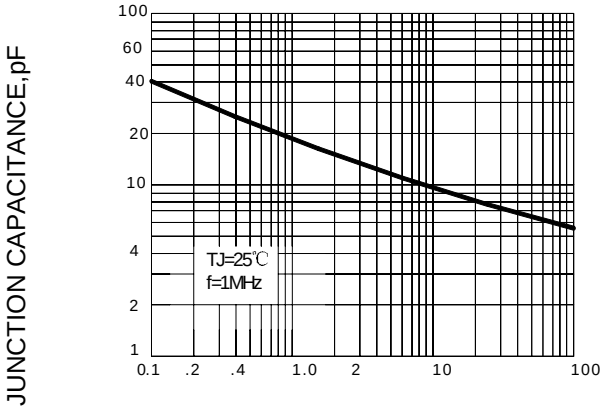

FIG.3 -- PEAK FORWARD SURGE CURRENT

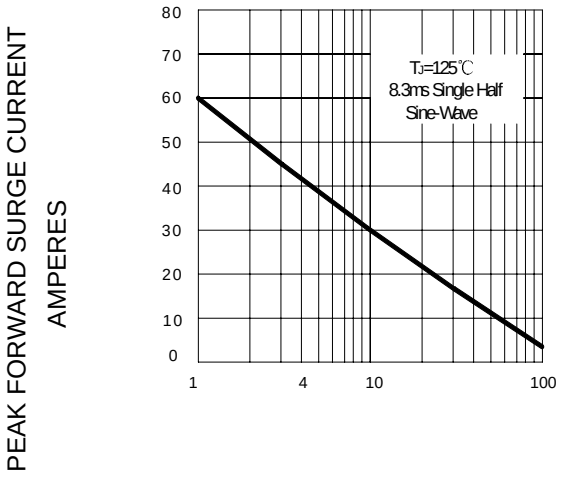

FIG.4 -- FORWARD DERATING CURVE